

/ Descriptions

SOP-8 P MOS

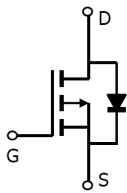
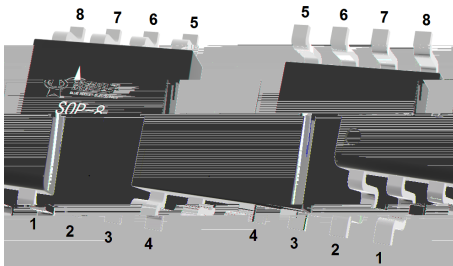
P-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

/ Features $V_{DS} (V) = -30V$ $I_D = -8.8 A$ $R_{DS(ON)} < 23m \quad (V_{GS} = -10V)$ $R_{DS(ON)} < 35m \quad (V_{GS} = -4.5V)$

HF Product.

/ Applications

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

/ Equivalent Circuit**/ Pinning**

PIN1	S	PIN 2	S	PIN 3	S	PIN 4	G
PIN 5	D	PIN 6	D	PIN 7	D	PIN 8	D

/ Marking

See Marking Instructions.

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current ^A		$I_D (T_a=25^\circ\text{C})$	-8.8	A
Continuous Drain Current ^A		$I_D (T_a=70^\circ\text{C})$	-7.0	A
Pulsed Drain Current ^B		I_{DM}	-50	A
Power Dissipation for Single Operation ^A		$P_D (T_a=25^\circ\text{C})$	2.5	W
Power Dissipation for Single Operation ^A		$P_D (T_a=70^\circ\text{C})$	1.2	W
Avalanche Current		I_{AR}	-20	A
Repetitive avalanche energy 0.3mH ^B		E_{AR}	50	mJ
Maximum Junction Temperature		T_j	150	
Storage Temperature Range		T_{stg}	-55 +150	
Thermal Resistance-Junction to Ambient ^A	$t \leq 10\text{s}$	R_{JA}	50	/W
Thermal Resistance-Junction to Ambient ^A	Steady State	R_{JA}	125	/W
Maximum Junction-to-Lead ^C		R_{JL}	25	/W

Note:

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t = 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

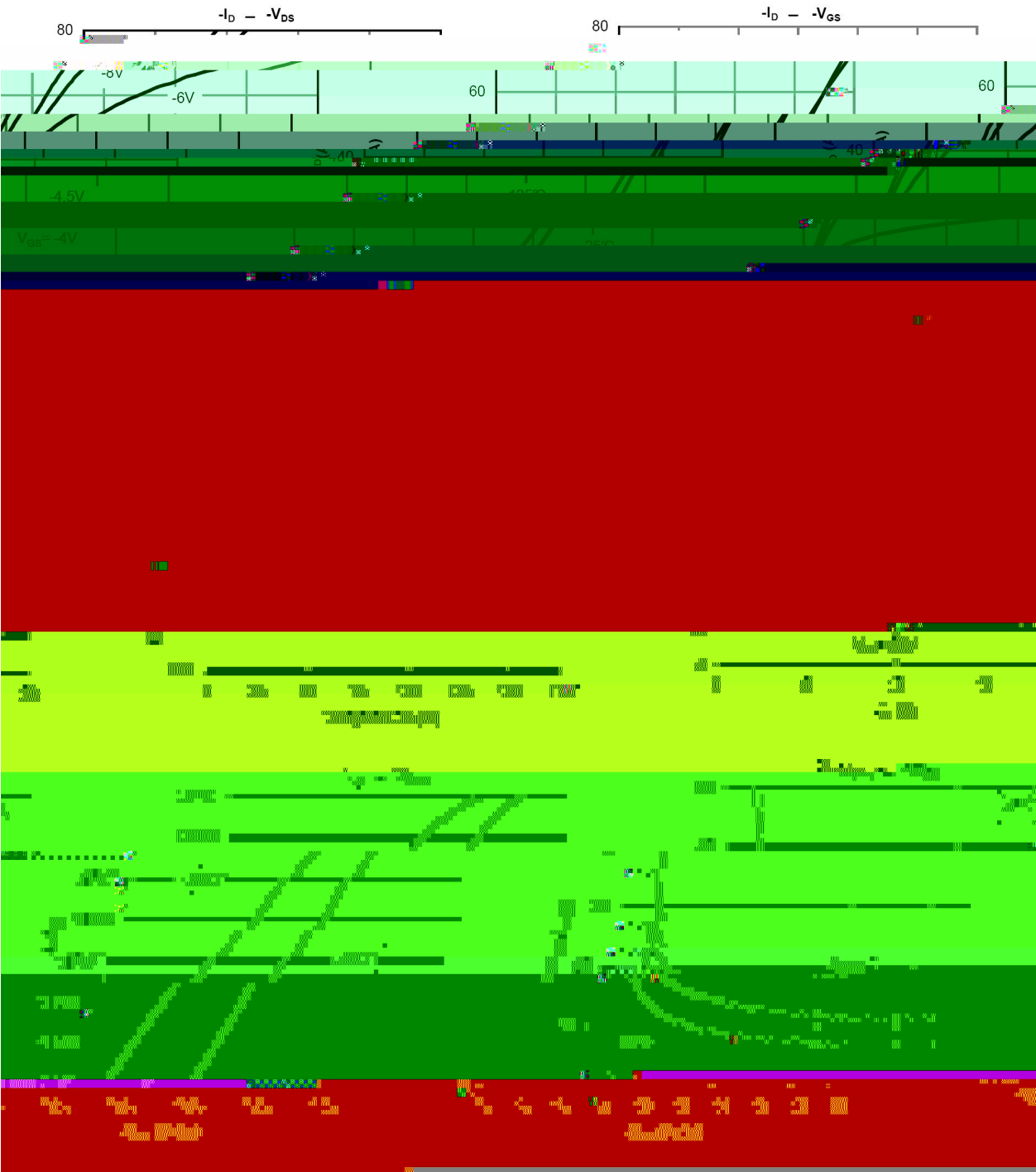
F: The current rating is based on the $t = 10\text{s}$ thermal resistance rating.

G: E_{AR} and I_{AR} ratings are based on low frequency and duty cycles to keep $T_j=25^\circ\text{C}$.

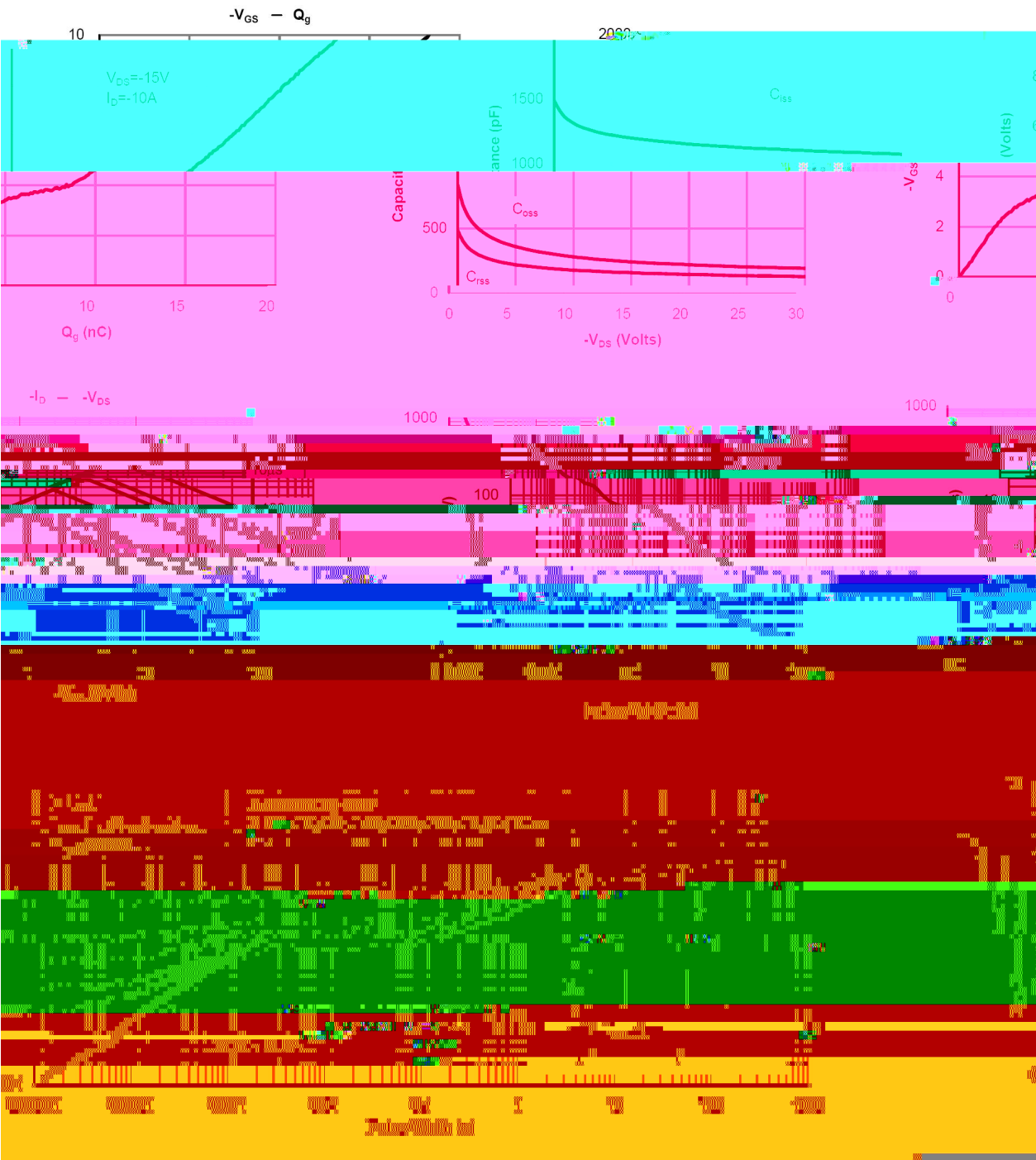
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D = -250\text{ A}$ $V_{GS} = 0V$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V$ $V_{GS} = 0V$			-1.0	A
		$V_{DS} = -30V$ $V_{GS} = 0V$ $T_J = 55^\circ C$			-5.0	
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V$ $V_{GS} = \pm 20V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ $I_D = -250\text{ A}$	-1.0	-1.7	-3.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V$ $I_D = -8.8A$		18	23	m
		$V_{GS} = -10V$ $I_D = -8.8A$ $T_J = 125^\circ C$		25	32	
		$V_{GS} = -4.5V$ $I_D = -6.7A$		27	35	
Forward Transconductance	g_{FS}	$V_{DS} = -5V$ $I_D = -8.8A$		12		S
Diode Forward Voltage	V_{SD}	$I_S = -2.1A$ $V_{GS} = 0V$		-0.73	-1.2	V
Maximum Body-Diode Continuous Current	I_S				-2.1	A
Total Gate Charge	Q_g	$V_{GS} = -5V$ $V_{DS} = -15V$ $I_D = -8.8A$		17	24	nC
Gate-Source Charge	Q_{gs}			5		
Gate-Drain Charge	Q_{gd}			6		
Input Capacitance	C_{iss}	$V_{GS} = 0V$ $V_{DS} = -15V$ $f = 1MHz$		1604		pF
Output Capacitance	C_{oss}			408		
Reverse Transfer Capacitance	C_{rss}			202		
Turn-on Delay Time	$t_{d(on)}$	$V_{GS} = -10V$ $V_{DS} = -15V$ $I_D = -1A$ $R_{GEN} = 6$		13	23	ns
Turn-on Rise Time	t_r			13.5	24	
Turn-off Delay Time	$t_{d(off)}$			42	68	
Turn-off Fall Time	t_f			25	40	

/ Electrical Characteristic Curve

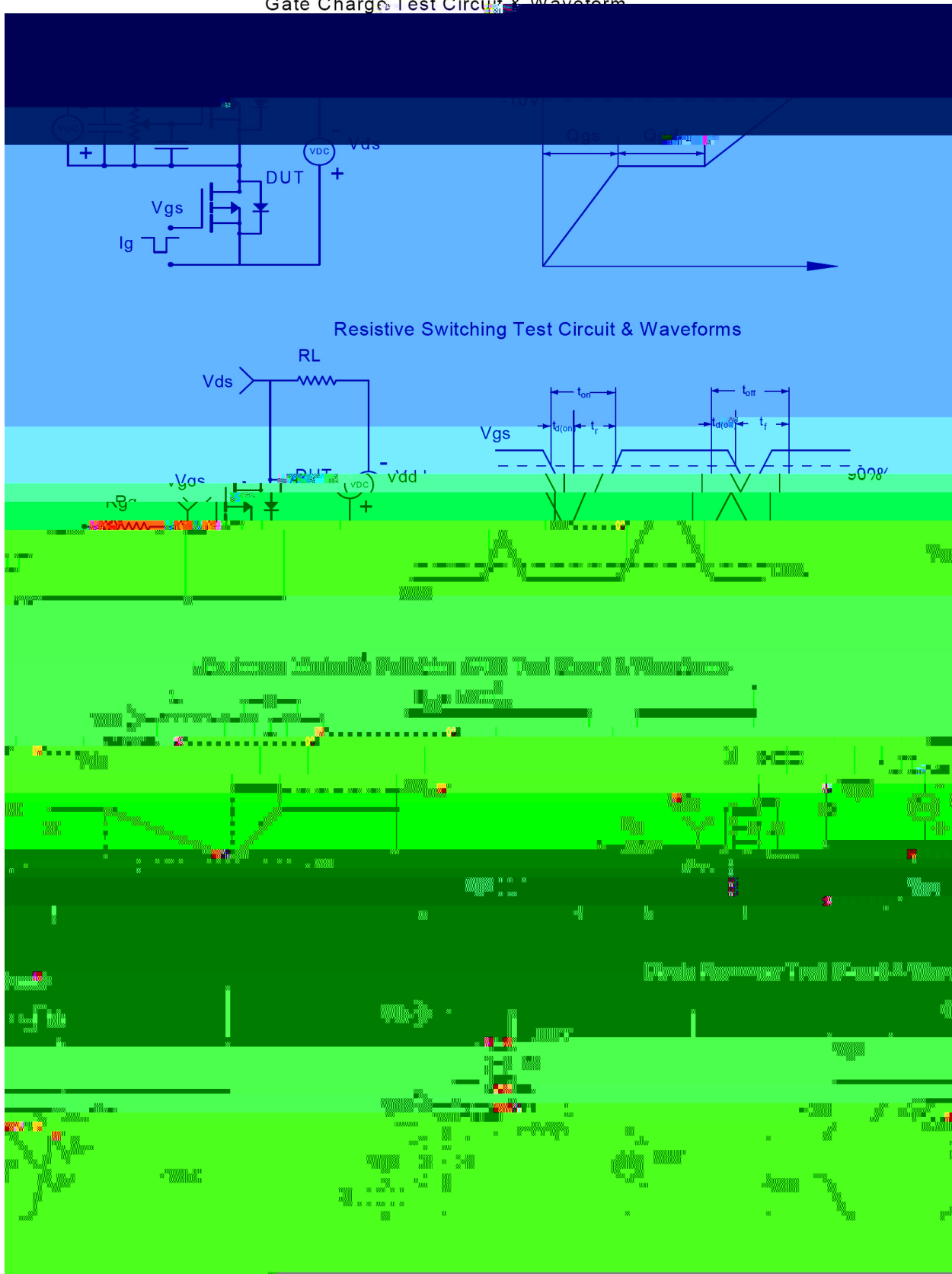


/ Electrical Characteristic Curve

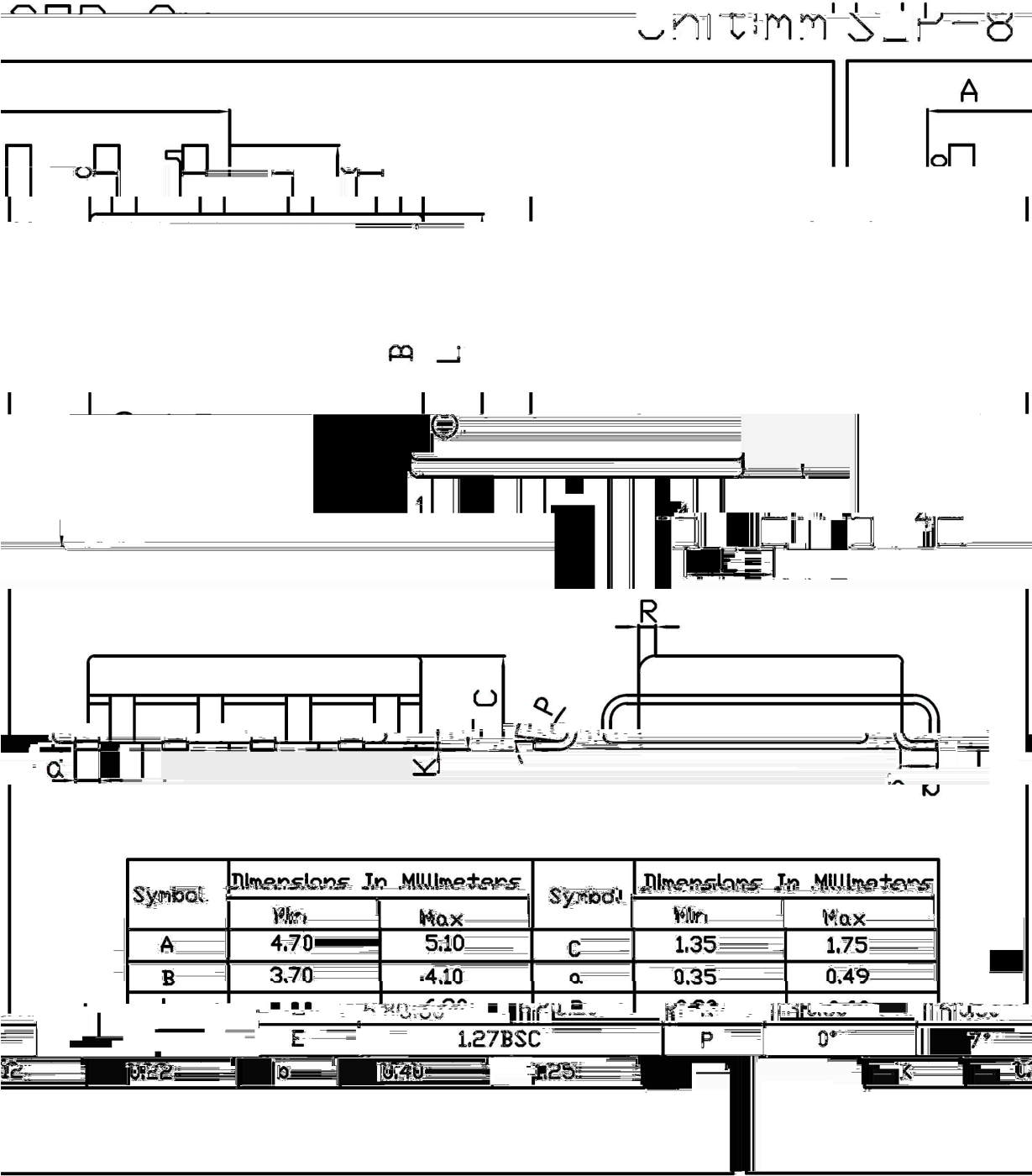


/ Test Waveform

Gate Charge Test Circuit & Waveform

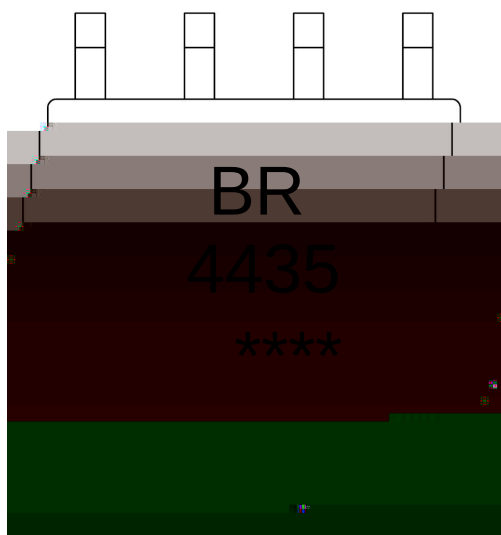


/ Package Dimensions





/ Marking Instructions



BR

4435

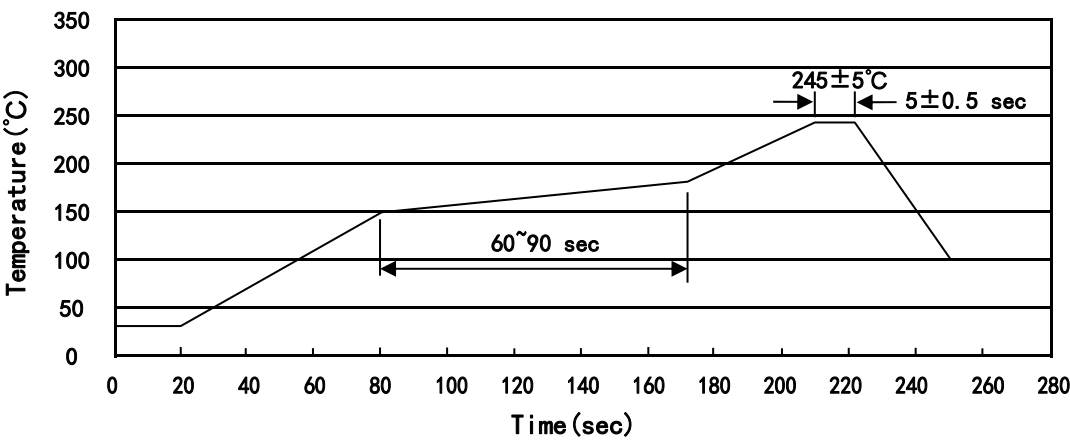
Note:

BR: Company Code

4435: Product Type Code

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOP/ESOP-8	4,000	2	8,000	6	48,000	13 ×12	360×360×50	380×335×366

/ Notices